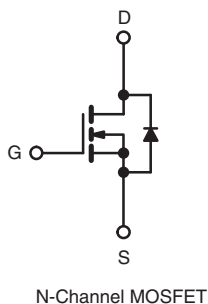
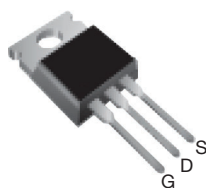


## Power MOSFET

### PRODUCT SUMMARY

|                           |                        |       |
|---------------------------|------------------------|-------|
| $V_{DS}$ (V)              | 60                     |       |
| $R_{DS(on)}$ ( $\Omega$ ) | $V_{GS} = 10\text{ V}$ | 0.028 |
| $Q_g$ (Max.) (nC)         | 67                     |       |
| $Q_{gs}$ (nC)             | 18                     |       |
| $Q_{gd}$ (nC)             | 25                     |       |
| Configuration             | Single                 |       |

**TO-220AB**


### FEATURES

- Dynamic  $dV/dt$  Rating
- 175 °C Operating Temperature
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Compliant to RoHS Directive 2002/95/EC



**RoHS\***  
COMPLIANT

### DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220AB package is universally preferred for commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220AB contribute to its wide acceptance throughout the industry.

### ORDERING INFORMATION

|                |            |
|----------------|------------|
| Package        | TO-220AB   |
| Lead (Pb)-free | IRFZ44PbF  |
|                | SiHFZ44-E3 |
| SnPb           | IRFZ44     |
|                | SiHFZ44    |

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

| PARAMETER   | SYMBOL           | LIMIT         | UNIT                  |
|---|------------------|---------------|-----------------------|
| Drain-Source Voltage                                      | $V_{DS}$         | 60            | V                     |
| Gate-Source Voltage                                       | $V_{GS}$         | $\pm 20$      |                       |
| Continuous Drain Current <sup>a</sup>                     | $I_D$            | 50            | A                     |
| Continuous Drain Current                                  |                  | 36            |                       |
| Pulsed Drain Current <sup>a</sup>                         | $I_{DM}$         | 200           |                       |
| Linear Derating Factor                                    |                  | 1.0           | W/ $^{\circ}\text{C}$ |
| Single Pulse Avalanche Energy <sup>b</sup>                | $E_{AS}$         | 100           | mJ                    |
| Maximum Power Dissipation                                 | $P_D$            | 150           | W                     |
| Peak Diode Recovery $dV/dt$ <sup>c</sup>                  | $dV/dt$          | 4.5           | V/ns                  |
| Operating Junction and Storage Temperature Range          | $T_J, T_{stg}$   | - 55 to + 175 | $^{\circ}\text{C}$    |
| Soldering Recommendations (Peak Temperature) <sup>d</sup> | for 10 s         | 300           |                       |
| Mounting Torque   | 6-32 or M3 screw | 10            | lbf · in              |
|   |                  | 1.1           | N · m                 |

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 25\text{ V}$ , starting  $T_J = 25\text{ }^{\circ}\text{C}$ ,  $L = 44\text{ }\mu\text{H}$ ,  $R_g = 25\text{ }\Omega$ ,  $I_{AS} = 51\text{ A}$  (see fig. 12).
- $I_{SD} \leq 51\text{ A}$ ,  $dI/dt \leq 250\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 175\text{ }^{\circ}\text{C}$ .
- 1.6 mm from case.
- Current limited by the package, (die current = 51 A).

\* Pb containing terminations are not RoHS compliant, exemptions may apply

**THERMAL RESISTANCE RATINGS**

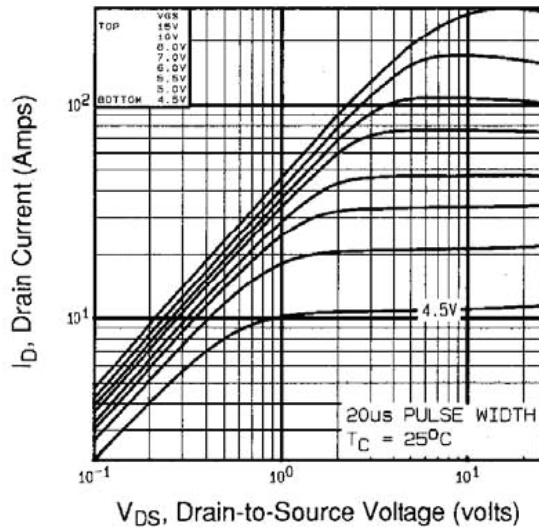
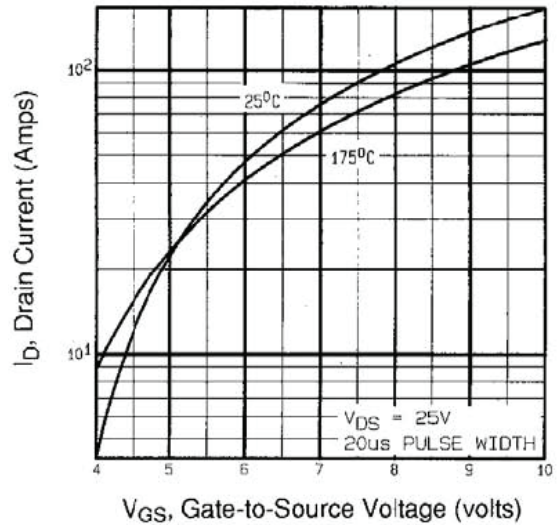
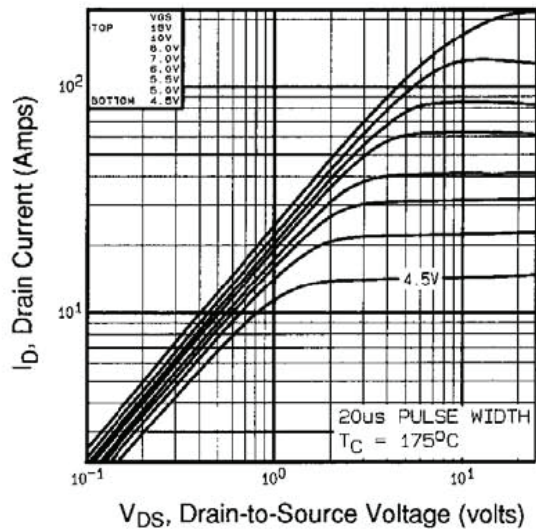
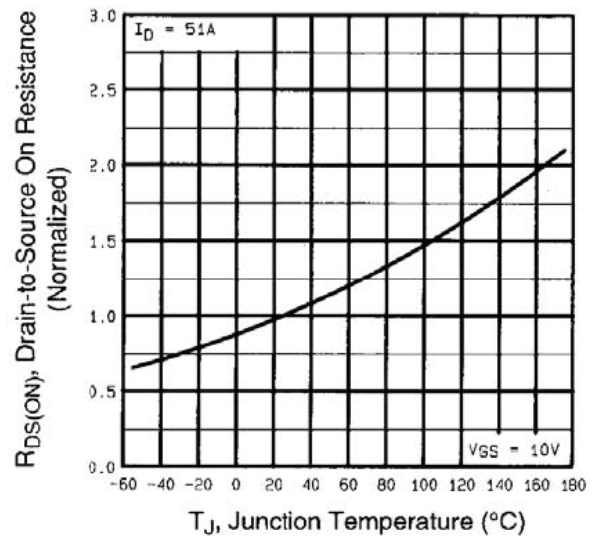
| PARAMETER                           | SYMBOL     | TYP. | MAX. | UNIT |
|-------------------------------------|------------|------|------|------|
| Maximum Junction-to-Ambient         | $R_{thJA}$ | -    | 62   | °C/W |
| Case-to-Sink, Flat, Greased Surface | $R_{thCS}$ | 0.50 | -    |      |
| Maximum Junction-to-Case (Drain)    | $R_{thJC}$ | -    | 1.0  |      |

**SPECIFICATIONS** ( $T_J = 25\text{ °C}$ , unless otherwise noted)

| PARAMETER                                 | SYMBOL                           | TEST CONDITIONS   |  | MIN. | TYP.  | MAX.  | UNIT |
|---|----------------------------------|---|--|------|-------|-------|------|
| Static                                    |                                  |   |  |      |       |       |      |
| Drain-Source Breakdown Voltage            | V <sub>DS</sub>                  | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA  |  | 60   | -     | -     | V    |
| V <sub>DS</sub> Temperature Coefficient   | ΔV <sub>DS</sub> /T <sub>J</sub> | Reference to 25 °C, I <sub>D</sub> = 1 mA   |  | -    | 0.060 | -     | V/°C |
| Gate-Source Threshold Voltage             | V <sub>GS(th)</sub>              | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA   |  | 2.0  | -     | 4.0   | V    |
| Gate-Source Leakage                       | I <sub>GSS</sub>                 | V <sub>GS</sub> = ± 20 V  |  | -    | -     | ± 100 | nA   |
| Zero Gate Voltage Drain Current           | I <sub>DSS</sub>                 | V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V   |  | -    | -     | 25    | μA   |
|   |                                  | V <sub>DS</sub> = 48 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C  |  | -    | -     | 250   |      |
| Drain-Source On-State Resistance          | R <sub>DS(on)</sub>              | V <sub>GS</sub> = 10 V  | I <sub>D</sub> = 31 A <sup>b</sup>   | -    | -     | 0.028 | Ω    |
| Forward Transconductance                  | g <sub>fs</sub>                  | V <sub>DS</sub> = 25 V, I <sub>D</sub> = 31 A   |  | 15   | -     | -     | S    |
| Dynamic                                   |                                  |   |  |      |       |       |      |
| Input Capacitance                         | C <sub>iss</sub>                 | V <sub>GS</sub> = 0 V,<br>V <sub>DS</sub> = 25 V,<br>f = 1.0 MHz, see fig. 5  |  | -    | 1900  | -     | pF   |
| Output Capacitance                        | C <sub>oss</sub>                 |   |  | -    | 920   | -     |      |
| Reverse Transfer Capacitance              | C <sub>rss</sub>                 |   |  | -    | 170   | -     |      |
| Total Gate Charge                         | Q <sub>g</sub>                   | V <sub>GS</sub> = 10 V  | I <sub>D</sub> = 51 A, V <sub>DS</sub> = 48 V,<br>see fig. 6 and 13 <sup>b</sup> | -    | -     | 67    | nC   |
| Gate-Source Charge                        | Q <sub>gs</sub>                  |   |  | -    | -     | 18    |      |
| Gate-Drain Charge                         | Q <sub>gd</sub>                  |   |  | -    | -     | 25    |      |
| Turn-On Delay Time                        | t <sub>d(on)</sub>               | V <sub>DD</sub> = 30 V, I <sub>D</sub> = 51 A,<br>R <sub>g</sub> = 9.1 Ω, R <sub>D</sub> = 0.55 Ω, see fig. 10 <sup>b</sup> |  | -    | 14    | -     | ns   |
| Rise Time                                 | t <sub>r</sub>                   |   |  | -    | 110   | -     |      |
| Turn-Off Delay Time                       | t <sub>d(off)</sub>              |   |  | -    | 45    | -     |      |
| Fall Time                                 | t <sub>f</sub>                   |   |  | -    | 92    | -     |      |
| Internal Drain Inductance                 | L <sub>D</sub>                   | Between lead,<br>6 mm (0.25") from<br>package and center of<br>die contact  |  | -    | 4.5   | -     | nH   |
| Internal Source Inductance                | L <sub>S</sub>                   |   |  | -    | 7.5   | -     |      |
| Drain-Source Body Diode Characteristics   |                                  |   |  |      |       |       |      |
| Continuous Source-Drain Diode Current     | I <sub>S</sub>                   | MOSFET symbol<br>showing the<br>integral reverse<br>p - n junction diode  |  | -    | -     | 50    | A    |
| Pulsed Diode Forward Current <sup>a</sup> | I <sub>SM</sub>                  |   |  | -    | -     | 200   |      |
| Body Diode Voltage                        | V <sub>SD</sub>                  | T <sub>J</sub> = 25 °C, I <sub>S</sub> = 51 A, V <sub>GS</sub> = 0 V <sup>b</sup>   |  | -    | -     | 2.5   | V    |
| Body Diode Reverse Recovery Time          | t <sub>rr</sub>                  | T <sub>J</sub> = 25 °C, I <sub>F</sub> = 51 A, dI/dt = 100 A/μs   |  | -    | 120   | 180   | ns   |
| Body Diode Reverse Recovery Charge        | Q <sub>rr</sub>                  |   |  | -    | 0.53  | 0.80  | nC   |
| Forward Turn-On Time                      | t <sub>on</sub>                  | Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> and L <sub>D</sub> )                           |  |      |       |       |      |

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).  
b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 Typical Output Characteristics,  $T_C = 25^\circ\text{C}$** 

**Fig. 3 Typical Transfer Characteristics**

**Fig. 2 Typical Output Characteristics,  $T_C = 175^\circ\text{C}$** 

**Fig. 4 Normalized On-Resistance vs. Temperature**

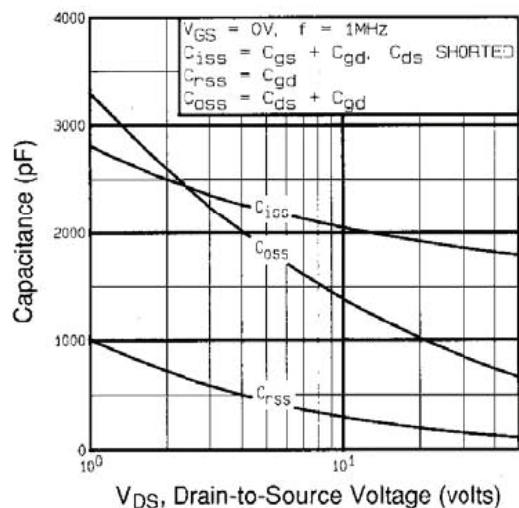


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

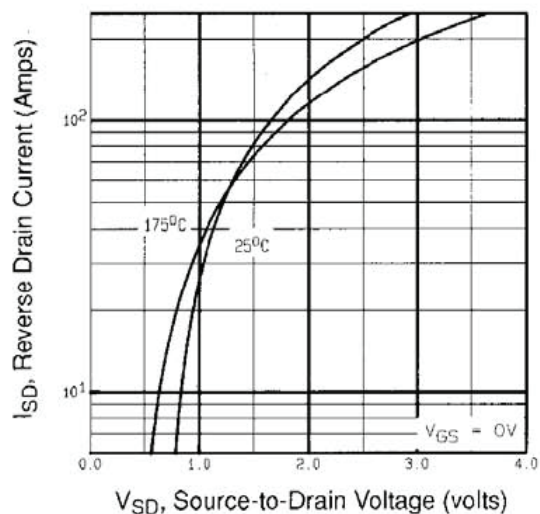


Fig. 7 - Typical Source-Drain Diode Forward Voltage

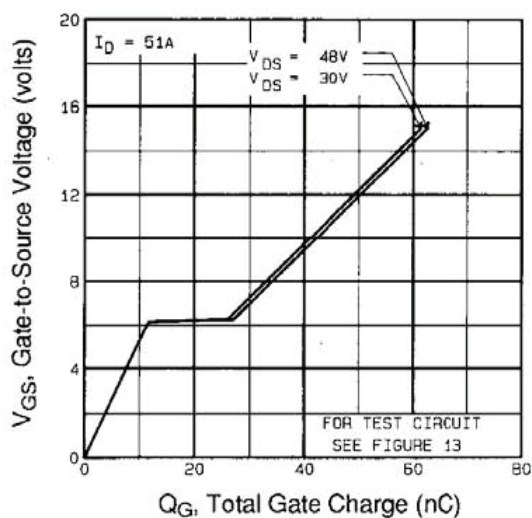


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

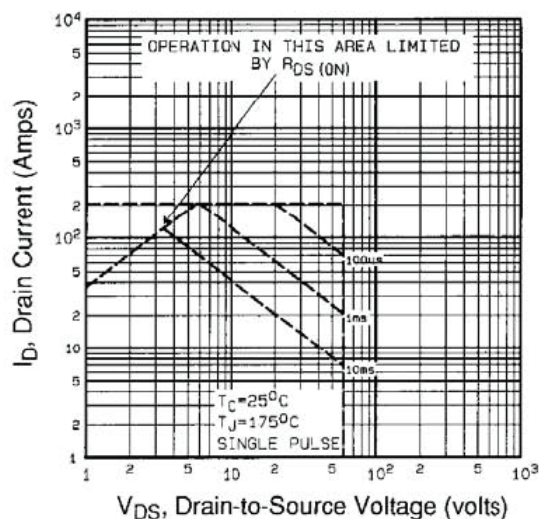


Fig. 8 - Maximum Safe Operating Area

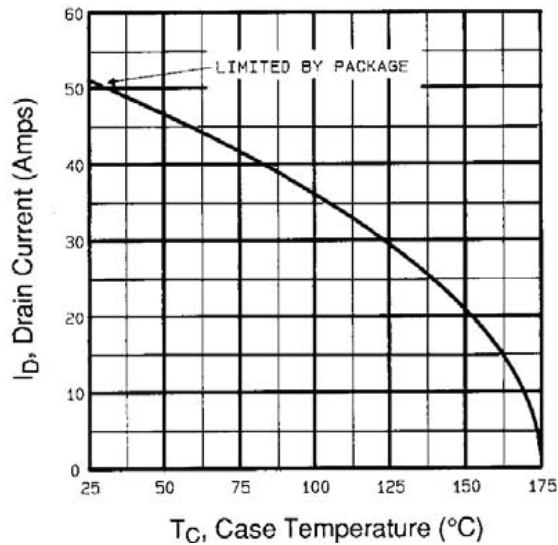


Fig. 9 - Maximum Drain Current vs. Case Temperature

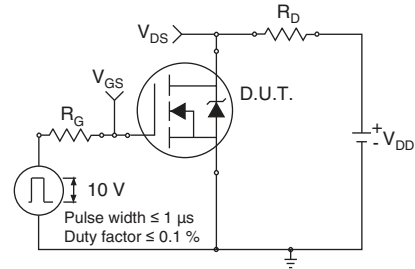


Fig. 10a - Switching Time Test Circuit

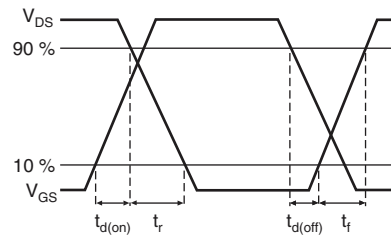


Fig. 10b - Switching Time Waveforms

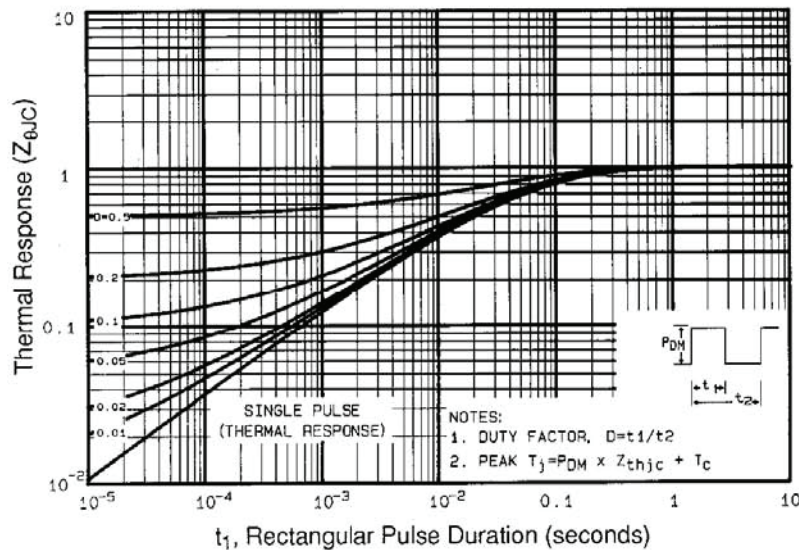


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

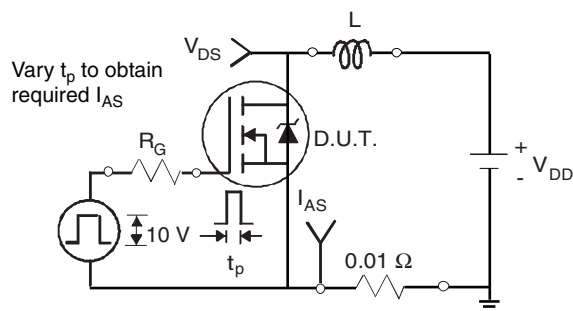


Fig. 12a - Unclamped Inductive Test Circuit

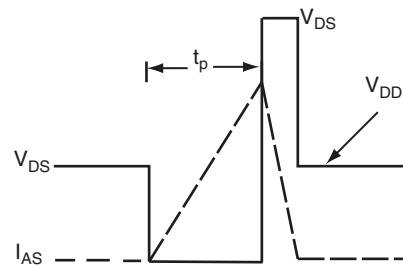


Fig. 12b - Unclamped Inductive Waveforms



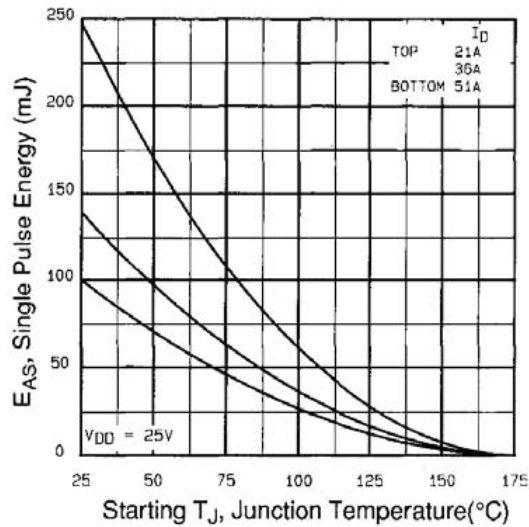


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

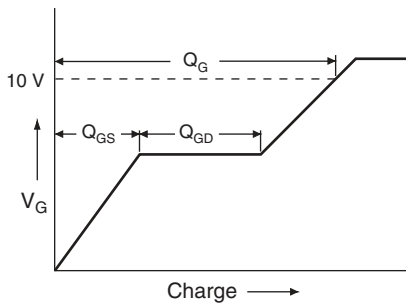


Fig. 13a - Basic Gate Charge Waveform

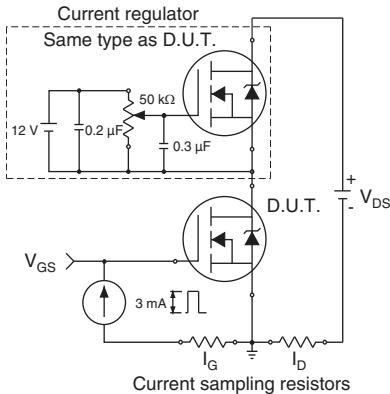
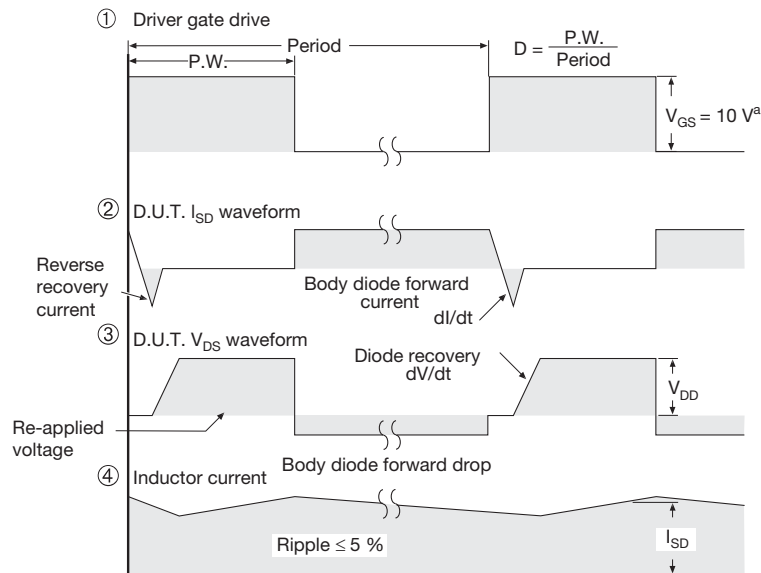
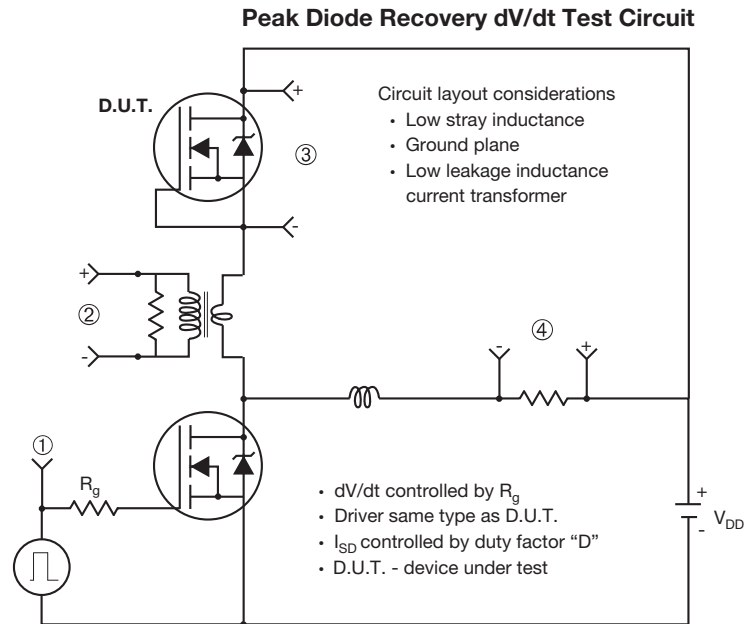


Fig. 13b - Gate Charge Test



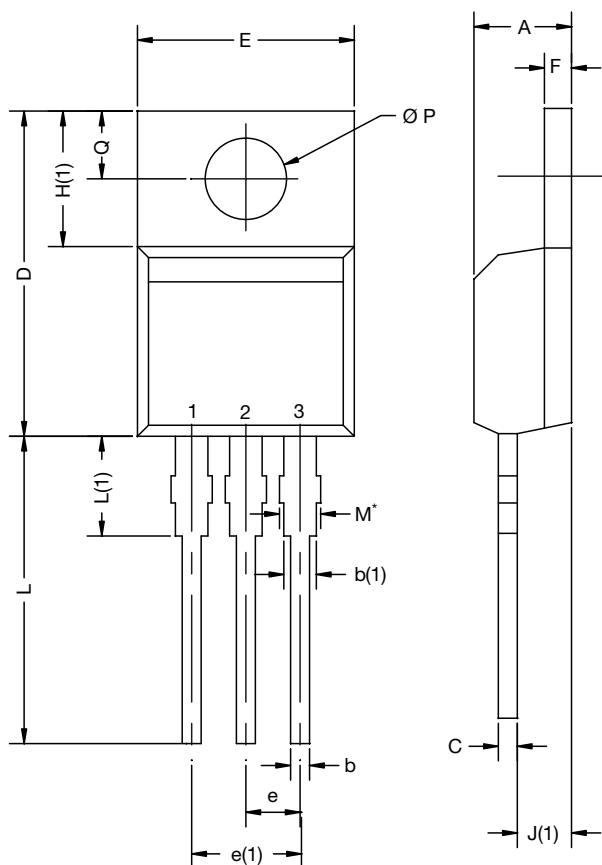
**Note**

a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 14 - For N-Channel**

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## TO-220-1

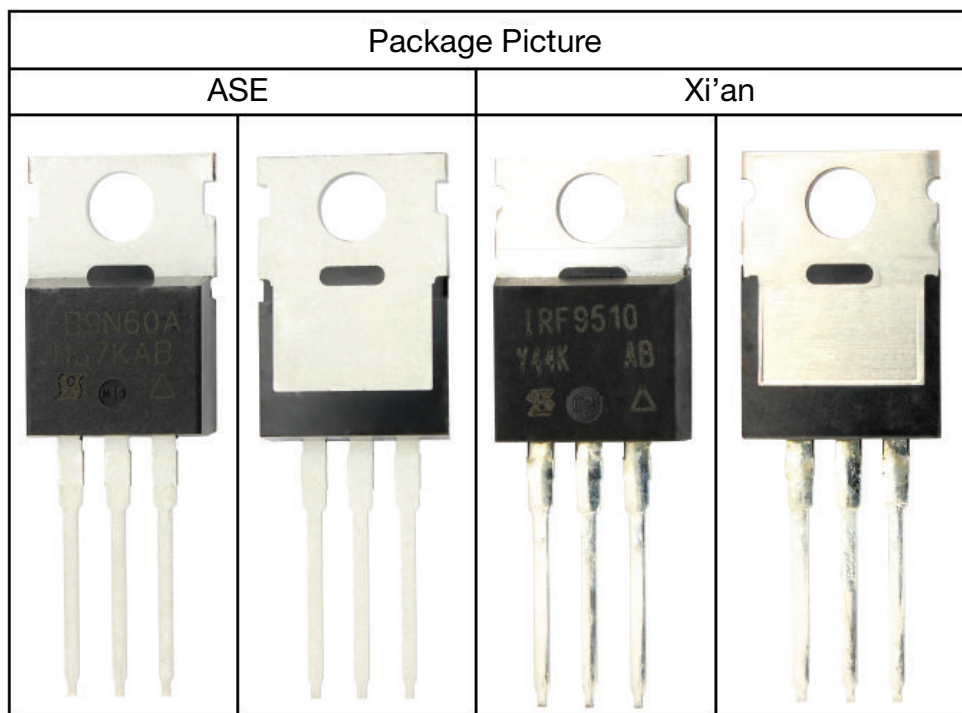


| DIM.            | MILLIMETERS |       | INCHES |       |
|-----------------|-------------|-------|--------|-------|
|                 | MIN.        | MAX.  | MIN.   | MAX.  |
| A               | 4.24        | 4.65  | 0.167  | 0.183 |
| b               | 0.69        | 1.02  | 0.027  | 0.040 |
| b(1)            | 1.14        | 1.78  | 0.045  | 0.070 |
| c               | 0.36        | 0.61  | 0.014  | 0.024 |
| D               | 14.33       | 15.85 | 0.564  | 0.624 |
| E               | 9.96        | 10.52 | 0.392  | 0.414 |
| e               | 2.41        | 2.67  | 0.095  | 0.105 |
| e(1)            | 4.88        | 5.28  | 0.192  | 0.208 |
| F               | 1.14        | 1.40  | 0.045  | 0.055 |
| H(1)            | 6.10        | 6.71  | 0.240  | 0.264 |
| J(1)            | 2.41        | 2.92  | 0.095  | 0.115 |
| L               | 13.36       | 14.40 | 0.526  | 0.567 |
| L(1)            | 3.33        | 4.04  | 0.131  | 0.159 |
| $\varnothing P$ | 3.53        | 3.94  | 0.139  | 0.155 |
| Q               | 2.54        | 3.00  | 0.100  | 0.118 |

ECN: X15-0364-Rev. C, 14-Dec-15  
DWG: 6031

### Note

- M\* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM







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